

In the Specification:

Please rewrite the title as follows:

INTEGRATED CIRCUIT ARRANGEMENT HAVING CAPACITORS
AND HAVING PREFERABLY PLANAR TRANSISTORS AND
FABRICATION METHOD

Please insert before the first paragraph of the application:

This application is the national stage application of international application number PCT/DE03/003354, filed on October 10, 2003, which claims the benefit of priority to German Patent Application 102 48 723.5, filed on October 18, 2002, incorporated herein by reference.

Please delete the paragraph on page 2, lines 4-7.

Please rewrite the paragraph on page 5, lines 1-11 as follows:

In a next development, spacers are arranged on both sides of the control electrode, which. The spacers also contain a different material or comprise a different material than the electrode layer, in particular a material which is not suitable as a starting point for an epitaxial layer growth during an epitaxy method for producing a semiconductor epitaxial layer, for example silicon nitride. The use of spacers means that side regions of the control electrode are covered, so that no epitaxy can proceed from there and short circuits are avoided.